

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1 - 5 (Cancelled).

6. (Currently Amended) A method for producing an epitaxial wafer by depositing a film of epitaxial layer through an epitaxial growth over a top surface of a silicon wafer, said method comprising:

~~a cleaning for~~ cleaning a top surface and a back ~~surfaces~~ surface of a silicon wafer with a SC-1 liquid and a SC-2 liquid;

a hydrophobicating cleaning, after said SC-1 and SC-2 liquid cleaning, for cleaning said back surface of said silicon wafer to be a water repellent surface; and

a hydrophilicating cleaning for cleaning said top surface of said silicon wafer to be a hydrophilic surface, wherein

after said SC-1 and SC-2 liquid cleaning, ~~said hydrophobicating~~ ~~hydrophibicating~~ cleaning, and said hydrophilicating cleaning are finished, a film of epitaxial layer is deposited through an epitaxial growth over said top surface of said silicon wafer, and wherein

said hydrophobicating cleaning and said hydrophilicating cleaning are simultaneously performed.

7. (Cancelled).

8. (Currently Amended) The method for producing an epitaxial wafer in accordance with claim 6, in which a contact angle of said hydrophilic surface and said top surface is 20° or smaller and a contact angle of said water repellent surface and said back surface is 30° or 30° or greater.

9. (Cancelled).

10. (Previously Presented) The method for producing an epitaxial wafer in accordance with claim 6, in which said hydrophilicating cleaning provides a cleaning by a combination of a sponge brush with a purified water.

11 – 12. (Cancelled).

13. (Previously Presented) The method for producing an epitaxial wafer in accordance with claim 6, in which said hydrophobicating cleaning is a cleaning using an HF solution or BHF solution.

14. (Previously Presented) The method for producing an epitaxial wafer in accordance with claim 8, in which said hydrophobicating cleaning is a cleaning using an HF solution or BHF solution.

15. (Previously Presented) The method for producing an epitaxial wafer in accordance with claim 10, in which said hydrophobicating cleaning is a cleaning using an HF solution or BHF solution.

16 – 18. (Cancelled).

19. (Previously Presented) The method for producing an epitaxial wafer in accordance with claim 8, in which said hydrophilicating cleaning provides a cleaning by a combination of a sponge brush with a purified water.

20. (Previously Presented) The method for producing an epitaxial wafer in accordance with claim 19, in which said hydrophobicating cleaning is a cleaning using an HF solution or BHF solution.